

*SPECIFICATION AMENDMENTS*

Replace the paragraph beginning at page 3, line 13 with:

A problem encountered with a prior art drive circuit constructed as above for driving a power semiconductor device is that when the drive circuit is applied to a high-voltage IGBT, a number of high-voltage diodes 5 need to be connected in series and this results in an increase in the total cost of the drive circuit and a reduction in the reliability of the drive circuit. Furthermore, in a high-voltage IGBT, the collector-emitter voltage doesn't change to a steady-state value (i.e., a value acquired according to the static characteristics of the IGBT) ~~at once and~~ instantaneously, but reaches the steady-state value at the expiration of a certain transition time interval after the IGBT has been turned on (according to circumstances, the collector voltage might still be ~~a voltage of tens~~ tens of volts at the expiration of 10 or more microseconds after the IGBT has been turned on). Another problem is ~~therefore~~ that ~~because~~ in order to distinguish normal turning-on from a short circuit, the above-mentioned transition time period needs to be masked, ~~the~~ so short-circuit detection by the collector voltage detector 6 is remarkably delayed and therefore the IGBT 1 cannot be protected.

Replace the paragraph beginning at page 7, line 13 with:

Fig. 18 is an explanatory drawing for showing the waveforms of the gate voltage and the gate current when the power semiconductor device is turned on with the power semiconductor device short-circuited;